

insulating layer therebetween,

wherein said channel semiconductor layer comprises a non-single crystalline silicon semiconductor layer containing oxygen, nitrogen or carbon at a concentration 5×10^{19} atoms/cm³ or less and said semiconductor layer shows a Raman [peak] shift at a wavenumber of 512 cm⁻¹ or higher.

25. (Amended) [The] A thin film transistor comprising:

a channel semiconductor layer [comprising];

a gate insulating layer contacting said channel layer; and

a gate electrode adjacent to said channel layer with said gate insulating layer therebetween,

wherein said channel semiconductor layer comprises a non-single crystalline silicon semiconductor layer containing oxygen, nitrogen or carbon at a concentration 5×10^{19} atoms/cm³ or less and a ratio of a full band width at half maximum (FWHM) of a Raman peak of said channel semiconductor layer to a FWHM of a Raman peak of a single crystalline silicon is less than 3.

27. (Amended) A thin film transistor comprising:

a channel semiconductor layer [comprising];

a gate insulating layer contacting said channel layer; and

a gate electrode adjacent to said channel layer with said gate insulating layer therebetween,

wherein said channel semiconductor layer comprises a non-single crystalline silicon semiconductor layer containing oxygen, nitrogen or carbon at a concentration 5×10^{19} atoms/cm³ or less and a peak intensity ratio I_a/I_c of said channel semiconductor layer is less than 0.4